

Dual P-Channel MOSFET

-60V, -12A, $68m\Omega$

FEATURES

- Fast switching
- Low thermal resistance package
- Low profile package
- Pb-free plating
- RoHS compliant
- Halogen-free package

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_{DS}		-60	V	
D (22.21)	V _{GS} = -10V	68	0	
$R_{DS(on)}$ (max)	$V_{GS} = -4.5V$	110	mΩ	
Q_g		16.4	nC	



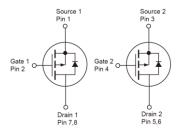




APPLICATION

- Power Supply
- Motor control





Dual P-Channel MOSFET

Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	I _D	-12	A	
Continuous Drain Current	$T_C = 100$ °C		-8		
Pulsed Drain Current (Note 2)		I _{DM}	-48	А	
Total Power Dissipation @ T _C = 25°C		P_{DTOT}	3.5	W	
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	7.2	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	12	А	
Operating Junction and Storage Temperatu	re Range	T_J, T_STG	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL LIMIT		UNIT	
Junction to Case Thermal Resistance	R _{eJC}	4.5	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	85	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.2	-1.6	-2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
7 0 1 1/1 5 1 0 1	$V_{DS} = -60V, V_{GS} = 0V$				-1	μА
Zero Gate Voltage Drain Current	V _{DS} = -48V, Tc = 125°C	I _{DSS}			-10	
	$V_{GS} = -10V, I_D = -6A$			54	68	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_{D} = -3A$	R _{DS(on)}		90	110	
Forward Transconductance	$V_{DS} = -10V, I_{D} = -6A$	g _{fs}		8.5		S
Dynamic (Note 5)						
Total Gate Charge		Q_g		16.4		nC
Gate-Source Charge	$V_{DS} = -30V, I_{D} = -6A,$ $V_{GS} = -10V$	Q_{gs}		2.8		
Gate-Drain Charge		Q_{gd}		3.6		
Input Capacitance		C _{iss}		870		
Output Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$	C _{oss}		70		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		42		
Switching (Note 6)				•	•	1
Turn-On Delay Time		t _{d(on)}		8.3		
Turn-On Rise Time	$V_{DD} = -30V$, $I_{D} = -1A$, $R_{GEN} = 6\Omega$	t _r		42.4		
Turn-Off Delay Time		t _{d(off)}		64.6		ns
Turn-Off Fall Time		t _f		16.4		
Source-Drain Diode (Note 4)						
Maximum Continuous Drain-Source	Integral reverse diode in the MOSFET				-12	A
Diode Forward Current		I _S			-12	_ ^
Maximum Pulse Drain-Source		I _{SM}			-48	Α
Diode Forward Current)/ O)/ I 4 4	-				
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = -1A$	V _{SD}			-1	V

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 0.1 mH, $I_{AS} = -12 A$, $V_{DD} = -25 V$, $R_G = 25 \Omega$, Starting $T_J = 25 ^{\circ} C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.



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ORDERING INFORMATION (EXAMPLE)

PART NO.		PACKAGE	PACKING		
	TSM680P06DPQ56 RLG	PDFN56	2,500pcs / 13"Reel		

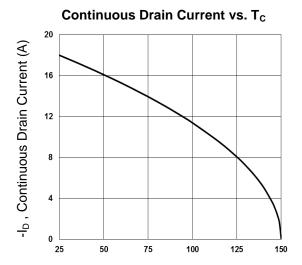
Note:

- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition

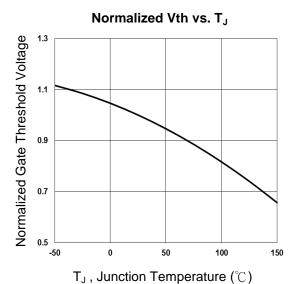


CHARACTERISTICS CURVES

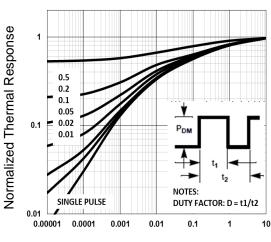
(T_C = 25°C unless otherwise noted)



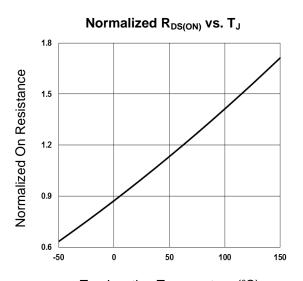
T_C, Case Temperature (°C)



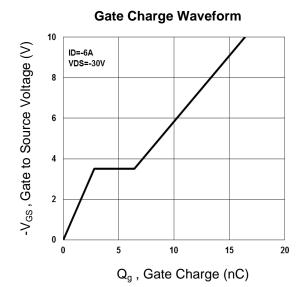
Normalized Transient Impedance



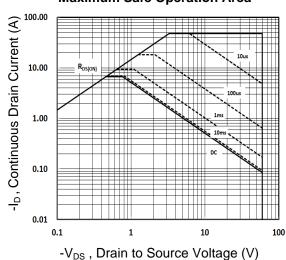
Square Wave Pulse Duration



T_J, Junction Temperature (°C)

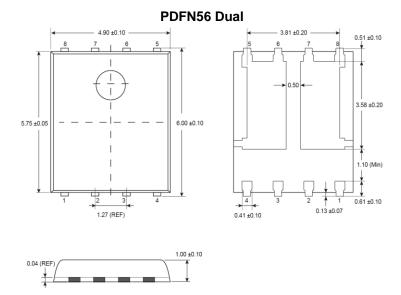


Maximum Safe Operation Area

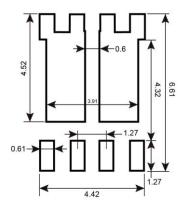




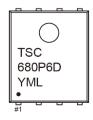
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

 \mathbf{L} = Lot Code (1~9, A~Z)



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